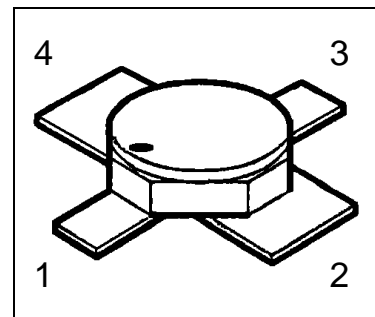


HiRel NPN Silicon RF Transistor

BFY450(ES)

Features

- For Medium Power Amplifiers
- Compression point $P_{-1dB} = 19$ dBm at 1.8 GHz
Max. available gain $G_{ma} = 16$ dB at 1.8 GHz
- Hermetically sealed microwave package
- Transition Frequency $f_T = 20$ GHz
- **SIEGET[®] 25-Line**
Infineon Technologies Grounded Emitter Transistor-
25 GHz f_T -Line



Product validation

-  **ESA Space Qualified**
ESCC Detail Spec. No.: 5611/008
Type Variant No. 03

Description

ESD: Electrostatic discharge sensitive device, observe handling precautions!

Table 1 Product information

Type	Comment	Pin Configuration				Package
		1	2	3	4	
BFY450(ES)	For flight use	C	E	B	E	Micro-X
BFY450(P) ¹	Not for flight use ¹					

¹ (P) parts have the same fit, form and function as (ES) parts, no screening acc. to Chart F3 in ESCC Generic Specification No. 5010

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Maximum ratings

1 Maximum ratings

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector-emitter voltage	V_{CE0}	-	-	4.5	V	
Collector-base voltage	V_{CBO}	-	-	15	V	
Emitter-base voltage	V_{EBO}	-	-	1.5	V	
Collector current	I_C	-	-	100	mA	
Base current	I_B	-	-	10	mA	
Total power dissipation ¹	P_{tot}	-	-	450	mW	$T_S \leq 110\text{ °C}$
Junction temperature	T_j	-	-	175	°C	
Operating temperature	T_{op}	-65	-	175	°C	
Storage temperature	T_{stg}	-65	-	175	°C	

¹ For $T_S > 110\text{ °C}$ derating is required. T_S is measured on the collector lead at the soldering point to the PCB

Thermal characteristics

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction –soldering point	$R_{th,JS}$	-	-	145	K/W	T_s is measured on the collector lead at the soldering point to the PCB
Soldering Temperature	T_{sol}	-	-	250	°C	Duration 5 seconds maximum at a distance of not less than 0.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Electrical characteristics

3 Electrical characteristics

at $T_A=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector-base cutoff current	I_{CBO}	-	-	100	nA	$V_{CB} = 5\text{V}, I_E = 0\text{A}$
Collector-emitter cutoff current ¹	I_{CEX}	-	-	200	μA	$V_{CE} = 4.5\text{V}, I_B = 1\mu\text{A}$
Emitter base cutoff current	I_{EBO}	-	-	50	μA	$V_{EB} = 1.5\text{V}, I_C = 0\text{A}$
DC current gain	h_{FE}	50	90	150	-	$I_C = 20\text{mA}, V_{CE} = 1\text{V}$

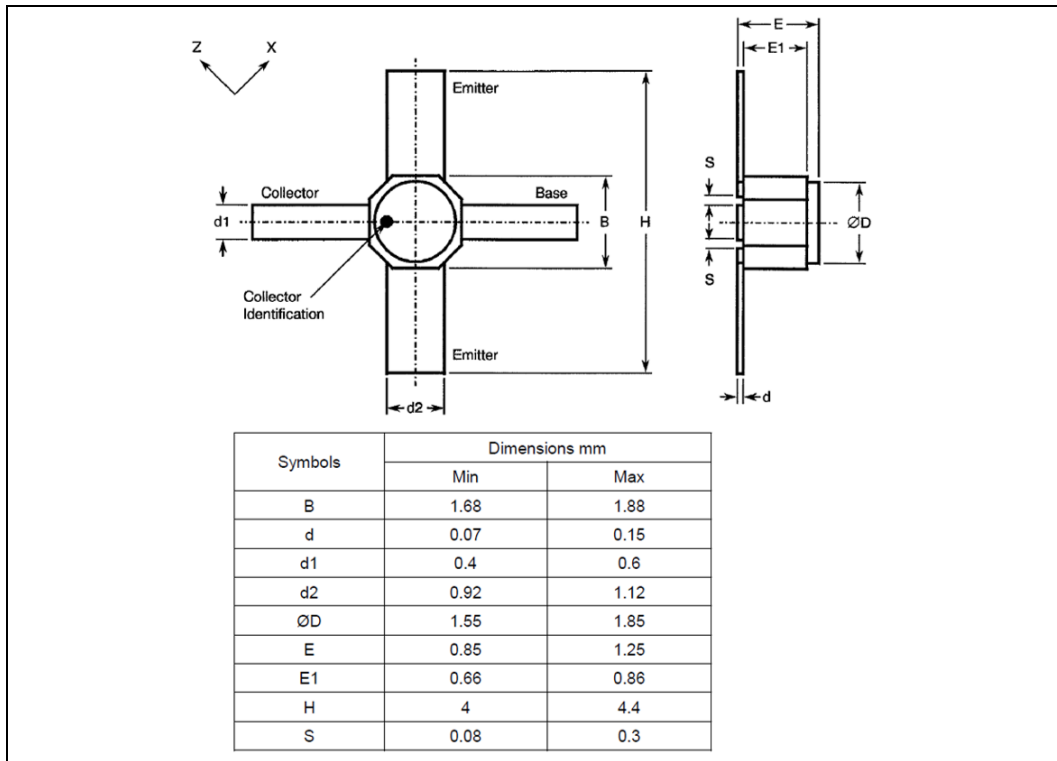
Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transition frequency	f_T	18 -	22 17	- -	GHz	$I_C = 90\text{mA}, V_{CE} = 3\text{V}, f = 1\text{GHz}$ $I_C = 90\text{mA}, V_{CE} = 3\text{V}, f = 2\text{GHz}$
Collector-base capacitance	C_{CB}	-	0.42	0.9	pF	$V_{CB} = 2\text{V}, V_{BE} = v_{be} = 0, f = 1\text{MHz}$
Collector-emitter capacitance	C_{CE}	-	1.27	2.6	pF	$V_{CE} = 2\text{V}, V_{BE} = v_{be} = 0, f = 1\text{MHz}$
Emitter-base capacitance	C_{EB}	-	2	3	pF	$V_{EB} = 0.5\text{V}, V_{CB} = v_{cb} = 0, f = 1\text{MHz}$
Noise Figure	F	-	1.25	2	dB	$I_C = 10\text{mA}, V_{CE} = 2\text{V}, f = 1.8\text{GHz},$ $Z_S = Z_{Sopt}$
Insertion power gain	$ S_{21e} ^2$	8	12	-	dB	$I_C = 50\text{mA}, V_{CE} = 2\text{V}, f = 1.8\text{GHz},$ $Z_S = Z_L = 50\Omega$
Power Gain ²	G_{ma}	-	16	-	dB	$I_C = 50\text{mA}, V_{CE} = 2\text{V}, f = 1.8\text{GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$
1dB Compression point	P_{-1dB}	-	19	-	dBm	$I_C = 50\text{mA}, V_{CE} = 2\text{V}, f = 1.8\text{GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$

¹ This test assures $V_{(BR)CE0} > 4.5\text{V}$

$$^2 G_{ma} = \left| \frac{S_{21}}{S_{12}} \right| (k - \sqrt{k^2 - 1}), G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$$

4 Package outlines



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